

# GaAs INTEGRATED CIRCUIT $\mu PG174TA$

### L-BAND PA DRIVER AMPLIFIER

#### DESCRIPTION

The  $\mu$ PG174TA is L-Band PA driver amplifier developed for digital cellular telephone and PCS applications. This device feature high output power and low distortion with 2.8 V low voltage and 35 mA low current operation. It is housed in a very small 6-pin minimold package available on tape-and-reel and easy to install and contributes to miniaturizing the systems.

#### FEATURES

- Low operation voltage :  $V_{DD} = 2.8 V$
- Low distortion : P<sub>adj1</sub> = -60 dBc TYP. @ V<sub>DD</sub> = 2.8 V, f<sub>RF</sub> = 1 429 to 1 453 MHz, P<sub>out</sub> = +10 dBm Off-chip input and output matching
- Low operation current : IDD = 35 mA TYP. @ VDD = 2.8 V, fRF = 1 429 to 1 453 MHz, Pout = +10 dBm Off-chip input and output matching
- 6-pin minimold package

#### APPLICATION

• Digital Cellular: PDC1.5G, DCS1800, PCS, etc.

#### **ORDERING INFORMATION**

| Part Number | Package        | Supplying Form              |  |
|-------------|----------------|-----------------------------|--|
| μPG174TA-E3 | 6-pin minimold | Carrier tape width is 8 mm. |  |
|             |                | Qty 3kp/reel.               |  |

**Remark** To order evaluation samples, please contact your local NEC sales office. (Part number for sample order:  $\mu$ PG174TA)

#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = +25°C)

| Parameters                    | Symbol | Ratings             | Unit |
|-------------------------------|--------|---------------------|------|
| Supply Voltage                | Vdd    | 6.0                 | V    |
| Input Power                   | Pin    | -10                 | dBm  |
| Total Power Dissipation       | Ptot   | 170 <sup>Note</sup> | mW   |
| Operating Ambient Temperature | TA     | -30 to +90          | °C   |
| Storage Temperature           | Tstg   | -35 to +150         | °C   |

Note Mounted on a  $50 \times 50 \times 1.6$  mm double copper clad epoxy glass PWB, T<sub>A</sub> = +85°C

## Caution The IC must be handled with care to prevent static discharge because its circuit composed of GaAs HJ-FET.

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#### PIN CONNECTION AND INTERNAL BLOCK DIAGRAM



| Pin No. | Connection |  |
|---------|------------|--|
| 1       | GND        |  |
| 2       | GND        |  |
| 3       | IN         |  |
| 4       | Vdd1       |  |
| 5       | GND        |  |
| 6       | VDD2 & OUT |  |

#### ★ RECOMMENDED OPERATING CONDITIONS (T<sub>A</sub> = +25°C)

| Parameters          | Symbol  | MIN. | TYP. | MAX. | Unit |
|---------------------|---------|------|------|------|------|
| Supply Voltage 1, 2 | Vdd1, 2 | +2.7 | +2.8 | +3.0 | V    |
| Input Power         | Pin     | -    | -22  | -20  | dBm  |

#### **★** ELECTRICAL CHARACTERISTICS

(Unless otherwise specified,  $T_A = +25$ °C,  $V_{DD1} = V_{DD2} = +2.8$  V,  $\pi/4DQPSK$  modulated signal input, off-chip input and output matching)

| Parameters                       | Symbol Test Conditions |  | MIN.  | TYP. | MAX.  | Unit |
|----------------------------------|------------------------|--|-------|------|-------|------|
| Operating Frequency              | f                      |  | 1 429 | -    | 1 453 | MHz  |
| Power Gain                       | G₽                     | Pin = −22 dBm                              | 32.0  | 34.0 | -     | dB   |
| Total Current                    | ldd                    | P <sub>in</sub> = −22 dBm                  | -     | 35   | 40    | mA   |
| Adjacent Channel Power Leakage 1 | P <sub>adj1</sub>      | $P_{out}$ = +10 dBm, $\Delta f$ = ±50 kHz  | -     | -60  | -55   | dBc  |
| Adjacent Channel Power Leakage 2 | P <sub>adj2</sub>      | $P_{out}$ = +10 dBm, $\Delta f$ = ±100 kHz | -     | -65  | -60   | dBc  |

#### **\*** REFERENCE CHARACTERISTICS

(Unless otherwise specified,  $T_A = +25^{\circ}C$ ,  $V_{DD1} = V_{DD2} = +2.8$  V, f = 1 429 to 1 453 MHz, off-chip input and output matching)

| Parameters         | Symbol | MIN. | TYP. | MAX. | Unit |
|--------------------|--------|------|------|------|------|
| Input Return Loss  | RLin   | -    | 10   | -    | dB   |
| Output Return Loss | RLout  | -    | 10   | -    | dB   |

#### **EVALUATION CIRCUIT**

VDD1 = VDD2 = +2.8 V, f = 1 429 to 1 453 MHz



Using the NEC Evaluation board

| Parts List | Value    |  |
|------------|----------|--|
| C1, C2     | 1 000 pF |  |
| C3         | 2.0 pF   |  |
| R1         | 10 Ω     |  |
| L1         | 6.8 nH   |  |
| L2         | 3.3 nH   |  |





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#### **\*** TYPICAL CHARACTERISTICS



Data Sheet P13230EJ2V0DS00



#### PACKAGE DIMENSIONS

#### 6 PIN MINIMOLD PACKAGE (UNIT: mm)



#### **RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

| Soldering Method | Soldering Conditions  | Recommended Condition Symbol |
|------------------|---|------------------------------|
| Infrared Reflow  | Package peak temperature: 235°C or below<br>Time: 30 seconds or less (at 210°C)<br>Count: 3, Exposure limit: None <sup>Note</sup> | IR35-00-3                    |
| VPS              | Package peak temperature: 215°C or below<br>Time: 40 seconds or less (at 200°C)<br>Count: 3, Exposure limit: None <sup>Note</sup> | VP15-00-3                    |
| Wave Soldering   | Soldering bath temperature: 260°C or below<br>Time: 10 seconds or less<br>Count: 1, Exposure limit: None <sup>Note</sup>          | WS60-00-1                    |
| Partial Heating  | Pin temperature: 300°C<br>Time: 3 seconds or less (per side of device)<br>Exposure limit: None <sup>Note</sup>                    | _                            |

Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

#### Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document **SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).** 

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#### Caution

The Great Care must be taken in dealing with the devices in this guide. The reason is that the material of the devices is GaAs (Gallium Arsenide), which is designated as harmful substance according to the law concerned. Keep the law concerned and so on, especially in case of removal.

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